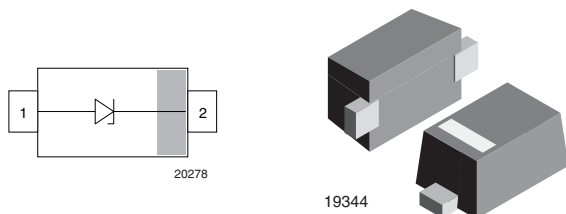




Single-Line ESD-Protection Diode in SOD-523



MARKING (example only)



Bar = cathode marking

X = date code

Y = type code (see table below)

FEATURES

- Compact SOD-523 package
- Low package height < 0.7 mm
- 1-line unidirectional ESD-protection
- AEC-Q101 qualified available
- Working range 1 V to 33 V
- ESD immunity acc. IEC 61000-4-2
±15 kV to ±30 kV contact discharge
±15 kV to ±30 kV air discharge
- Lead plating: Sn (e3)
- soldering can be checked by standard vision inspection
- AOI = Automated Optical Inspection
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



DESIGN SUPPORT TOOLS click logo to get started



ORDERING INFORMATION

PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	ENVIRONMENTAL AND QUALITY CODE			ORDERING CODE (EXAMPLE)
		RoHS COMPLIANT + LEAD (Pb)-FREE TERMINATIONS	TIN PLATED	8K PER 7" REEL (8 mm TAPE)	
		GREEN		MOQ = 8K/BOX	
VESD05C1-02V	-	G	3	-08	VESD05C1-02V-G3-08
VESD05C1-02V	H	G	3	-08	VESD05C1-02VHG3-08

PACKAGE DATA

DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
VESD01C1-02V	SOD-523	. V	1.32 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	Peak temperature max. 260 °C
VESD03C1-02V		. B				
VESD05C1-02V		. C				
VESD08C1-02V		. D				
VESD012C1-02V		. E				
VESD016C1-02V		. G				
VESD026C1-02V		. X				
VESD033C1-02V		A				

**ABSOLUTE MAXIMUM RATINGS VESD01C1-02V**(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	14.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD03C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	11.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD05C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	8.7	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD08C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	6.60	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

**ABSOLUTE MAXIMUM RATINGS VESD12C1-02V**(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	4.4	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD16C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	3.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	30	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		30	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD26C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	2.1	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	20	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		20	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

ABSOLUTE MAXIMUM RATINGS VESD33C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I _{PPM}	1.6	A
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P _{PP}	100	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	15	kV
	Air discharge acc. IEC 61000-4-2; 10 pulses		15	kV
Operating temperature	Junction temperature	T _J	-55 to +150	°C
Storage temperature		T _{stg}	-55 to +150	°C

**ELECTRICAL CHARACTERISTICS VESD01C1-02V**(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	1	V
Reverse voltage	at I _R = 100 µA	V _R	1	1.2	-	V
Reverse current	at V _R = 1 V	I _R	-	20	100	µA
Reverse breakdown voltage	at I _R = 20 mA	V _{BR}	2.5	2.65	2.8	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 14.6 A, t _p = 8/20 µs	V _C	-	6.2	6.9	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 14.6 A, t _p = 8/20 µs	V _F	-	3	3.92	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.13	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	153	192	230	pF

ELECTRICAL CHARACTERISTICS VESD03C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	3	V
Reverse voltage	at I _R = 20 µA	V _R	3	-	-	V
Reverse current	at V _R = 3 V	I _R	-	8	20	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4.4	4.65	4.9	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 11.6 A, t _p = 8/20 µs	V _C	-	7.8	8.70	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 11.6 A, t _p = 8/20 µs	V _F	-	2.6	3.32	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.19	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	89	112	135	pF

ELECTRICAL CHARACTERISTICS VESD05C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	5	V
Reverse voltage	at I _R = 1 µA	V _R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	0.01	0.1	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6.85	7.26	7.65	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 8.7 A, t _p = 8/20 µs	V _C	-	10.3	11.5	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 8.7 A, t _p = 8/20 µs	V _F	-	2.2	2.74	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.2	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	53	67	81	pF

**ELECTRICAL CHARACTERISTICS VESD08C1-02V**(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	8	V
Reverse voltage	at I _R = 0.1 µA	V _R	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	0.01	0.1	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9.5	10	10.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 6.6 A, t _p = 8/20 µs	V _C	-	13.7	15.3	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 6.6 A, t _p = 8/20 µs	V _F	-	1.9	2.32	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.23	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	37	47	57	pF

ELECTRICAL CHARACTERISTICS VESD12C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	12	V
Reverse voltage	at I _R = 0.1 µA	V _R	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	0.01	0.1	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.9	14.7	15.5	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 4.4 A, t _p = 8/20 µs	V _C	-	20.5	22.7	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 4.4 A, t _p = 8/20 µs	V _F	-	1.6	1.88	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.4	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	26	33	40	pF

ELECTRICAL CHARACTERISTICS VESD16C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	16	V
Reverse voltage	at I _R = 0.1 µA	V _R	16	-	-	V
Reverse current	at V _R = 16 V	I _R	-	0.01	0.1	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	17	17.9	18.8	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 3.6 A, t _p = 8/20 µs	V _C	-	25.3	28	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 3.6 A, t _p = 8/20 µs	V _F	-	1.5	1.72	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	0.53	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	21	27	33	pF

**ELECTRICAL CHARACTERISTICS VESD26C1-02V**(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	26	V
Reverse voltage	at I _R = 0.1 µA	V _R	26	-	-	V
Reverse current	at V _R = 26 V	I _R	-	< 0.01	0.1	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27.6	29.1	30.6	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 2.1 A, t _p = 8/20 µs	V _C	-	43	48	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 2.1 A, t _p = 8/20 µs	V _F	-	1.3	1.42	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	1.9	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	14	17.5	21	pF

ELECTRICAL CHARACTERISTICS VESD33C1-02V(T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITIONS / REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand off voltage	Max. reverse working voltage	V _{RWM}	-	-	33	V
Reverse voltage	at I _R = 0.1 µA	V _R	33	-	-	V
Reverse current	at V _R = 33 V	I _R	-	< 0.01	0.1	µA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	35.5	37.4	39.3	V
Reverse clamping voltage	at I _{PP} = I _{PPM} = 1.6 A, t _p = 8/20 µs	V _C	-	56	62.5	V
Forward clamping voltage	at I _{PP} = 1 A, t _p = 300 µs	V _F	0.9	1.1	1.2	V
	at I _{PP} = I _{PPM} = 1.6 A, t _p = 8/20 µs	V _F	-	1.22	1.32	V
Dynamic resistance	t _p = 100 ns (TLP; pin 2-1)	r _{dyn}	-	3.6	-	Ω
Capacitance	at V _R = 0 V; f = 1 MHz	C _D	12	15	18	pF

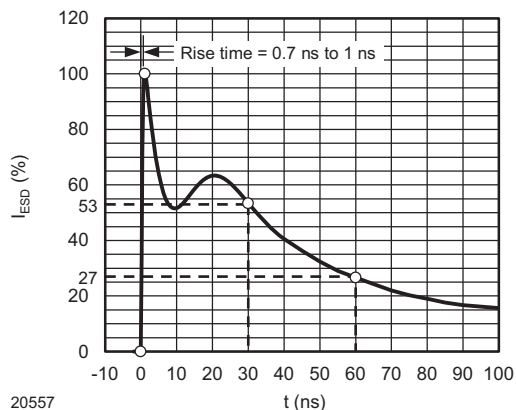


Fig. 1 - ESD Discharge Current Wave Form acc. IEC 61000-4-2 (330 Ω / 150 pF)

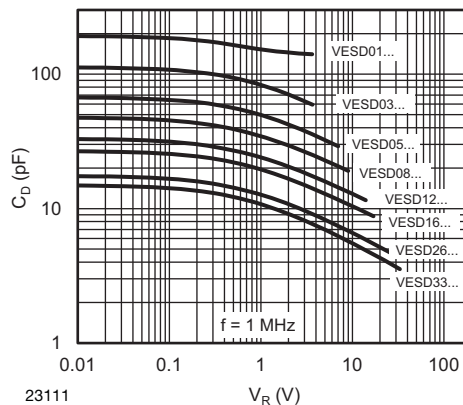


Fig. 4 - Typical Capacitance vs. Reverse Voltage

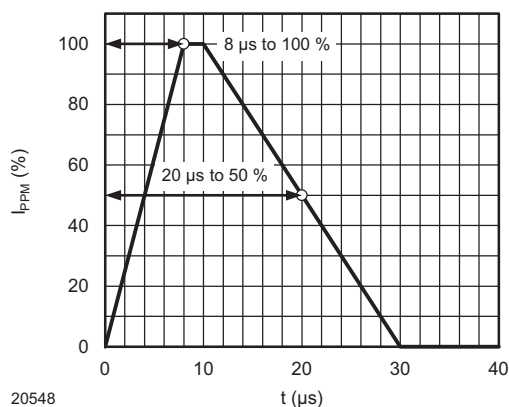


Fig. 2 - 8/20 μ s Peak Pulse Current Wave Form acc. IEC 61000-4-5

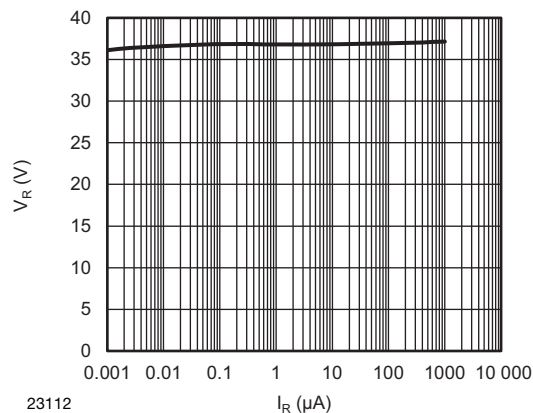


Fig. 5 - Typical Reverse Voltage vs. Reverse Current

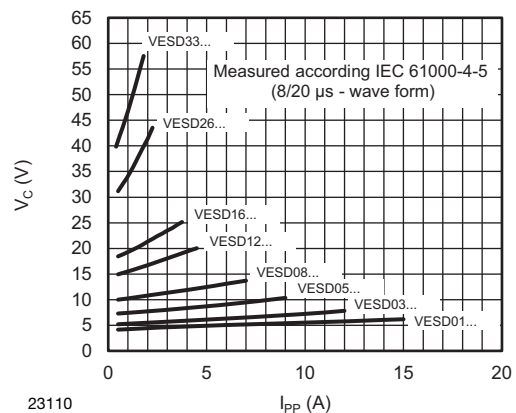


Fig. 3 - Typical Peak Clamping Voltage vs. Peak Pulse Current

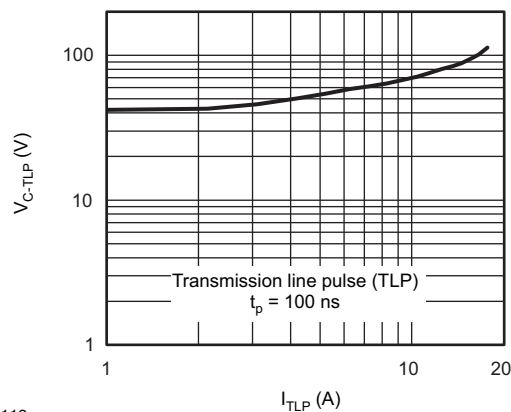


Fig. 6 - Typical Clamping Voltage vs. Peak Pulse Current

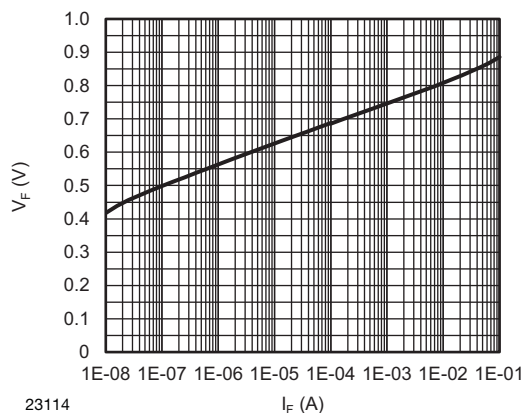


Fig. 7 - Typical Forward Voltage vs. Forward Current

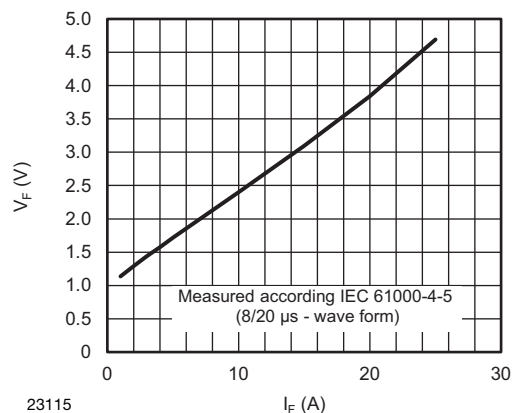
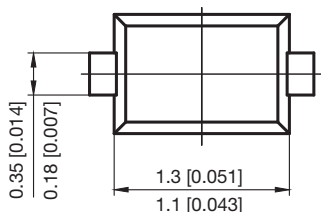
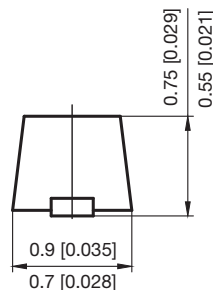
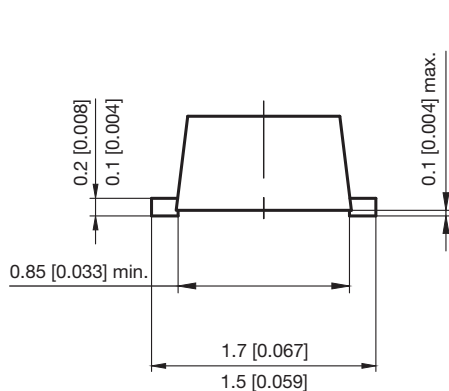
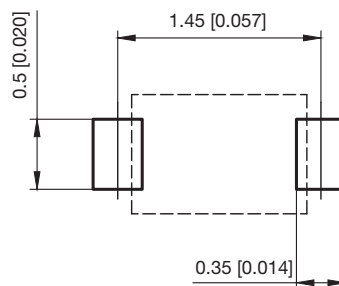


Fig. 8 - Typical Forward Voltage vs. Forward Current

PACKAGE DIMENSIONS in millimeters (Inches): **SOD-523**


foot print recommendation:



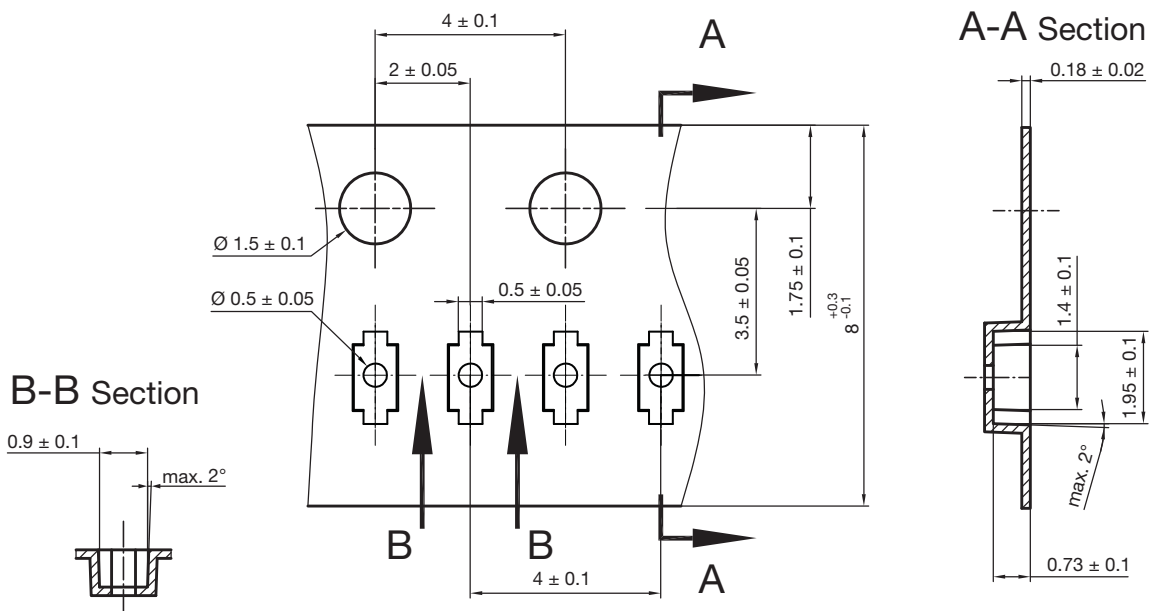
Document no.: S8-V-3880.02-003 (4)

Rev.2 - Date: 18. Aug. 2017

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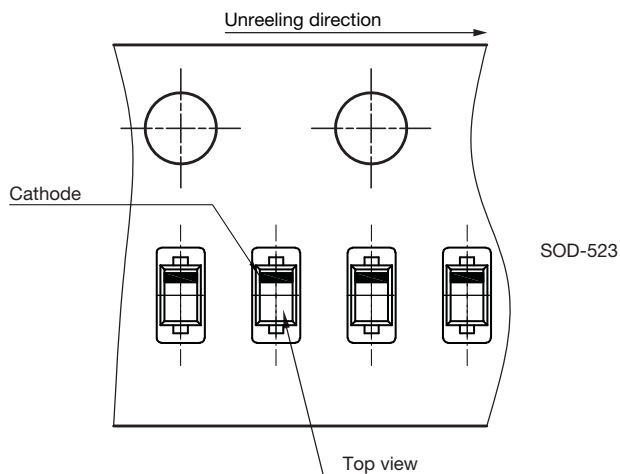


CARRIER TAPE SOD-523



S8-V-3717.03-005 (4)
05.07.2018
22959

ORIENTATION IN CARRIER TAPE SOD-523



S8-V-3717.03-006 (4)
05.07.2018
22958



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На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9